

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	107	(("6635583B2") or ("6624064B1") or ("6573030") or ("6541397B1") or ("6458516B1") or ("6423384B1") or ("6413852") or ("6380106") or ("6358573B1") or ("6333255") or ("6331380B1") or ("6323119B1") or ("6316347") or ("6291334B1") or ("6235629") or ("6214730") or ("6211065B1") or ("6165890") or ("6153935") or ("6143476") or ("6140226") or ("6140224") or ("6098568") or ("6080529") or ("6066577") or ("6064118") or ("6057226") or ("6035803") or ("6030901") or ("6008140") or ("5986344") or ("5900288") or ("5866920") or ("5789320") or ("5759913") or ("5461003") or ("6852647") or ("6624064") or ("6596627") or ("6541842") or ("6428894") or ("6358804") or ("6346747") or ("6214637") or ("6203898") or ("6184572") or ("6183930") or ("6054379") or ("5930655") or ("5981000") or ("5882830") or ("5830332") or ("5262262") or ("5022959") or ("5674573") or ("5998100") or ("6352922") or ("6653735") or ("DE10328578") or ("EP381109") or ("EP901156") or ("JP9045633") or ("JP11026578") or ("4975144") or ("6043167") or ("6428894") or ("6884733")).PN. or ((2003/0091938A1) or (2002/0090794A1) or (2002/0086547A1) or (2002/0001778A1) or (2001/0007788A1) or (2004/0038537A1) or (2004/0023502) or (2004/0166691A1) or (2004/0180551A1) or (2004/0038537) or (2004/0229470)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/30 08:12

EAST Search History

S2	7	S1 and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:22
S3	6	S1 and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:23
S4	1	S1 and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:37
S5	6	(substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric and "dual frequency"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 10:52

EAST Search History

S6	2	(substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric and "dual frequency" and ("ARC" or "anti reflective coating")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 08:41
S7	1	10/799146	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 10:52
S8	5	((substrate or semiconductor or wafer) near8 chamber) and (hydrocarbon near8 gas) and argon and plasma and (dual near4 frequency) and (amorphous near4 carbon) and hydrogen and (dielectric or oxide or insulat\$4) and etch\$3 and silicon and oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/30 08:25
S9	4	((substrate or semiconductor or wafer) near8 chamber) and (hydrocarbon near8 gas) and argon and plasma and (dual near4 frequency) and (amorphous near4 carbon) and hydrogen and (dielectric or oxide or insulat\$4) and etch\$3 and silicon and oxygen and (conduct\$4 or metal or polysilicon) and pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/30 08:26